



Academia-Industry Matching Event Second Special Workshop on Neutron Detection with MPGDs



Thin film Boron deposition for GEM-based neutron detectors

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CERN, 16-17 March 2015

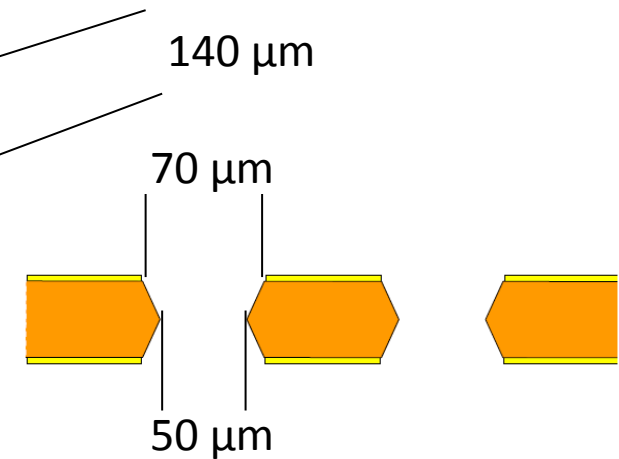
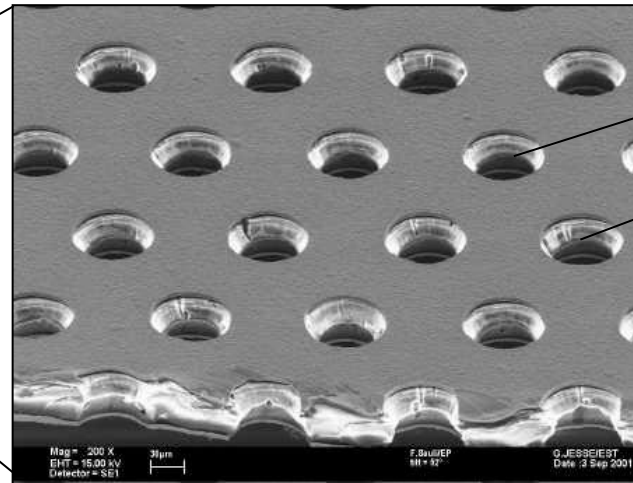
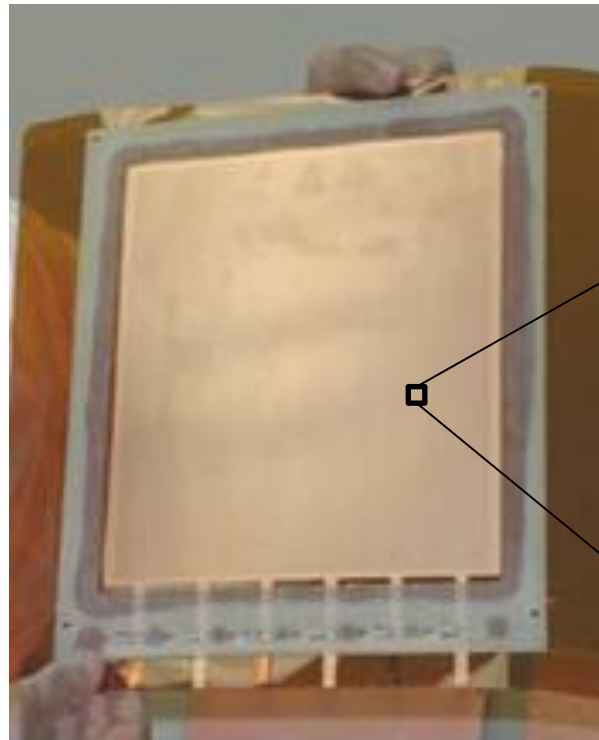
- ✓ **Side-on GEM-based thermal neutron detectors**
- ✓ **Pure ^{10}B (rather than B_4C) deposition activity**
 - ✓ **Deposition facilities**
 - ✓ **Characterization tools**
- ✓ **A brief overview on results and perspectives**



Gas Electron Multipliers (GEM)

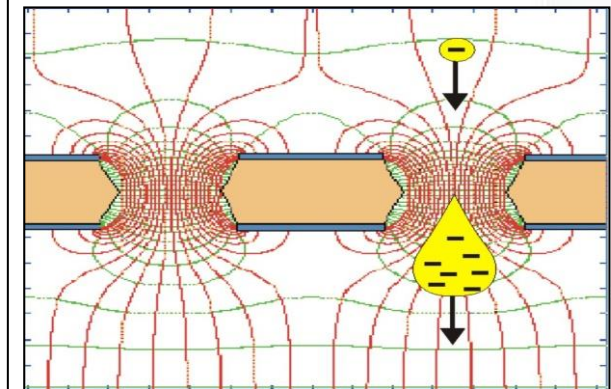
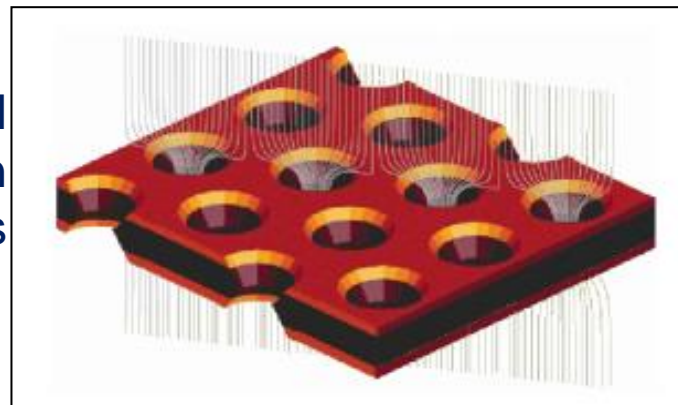


A Gas Electron Multiplier (F.Sauli, NIM A **386**, 531) is made by 50 μm thick kapton foil, copper clad (5 μm thick) on each side and perforated by an high surface-density of bi-conical channels;



Applying a potential difference (typically between 300 and 500 volts) between the two copper cladding, an high intensity electric field is produced inside the holes (80-100 kV/cm).

GEM is used as a proportional amplifier of the ionization charge released in a gas detector.



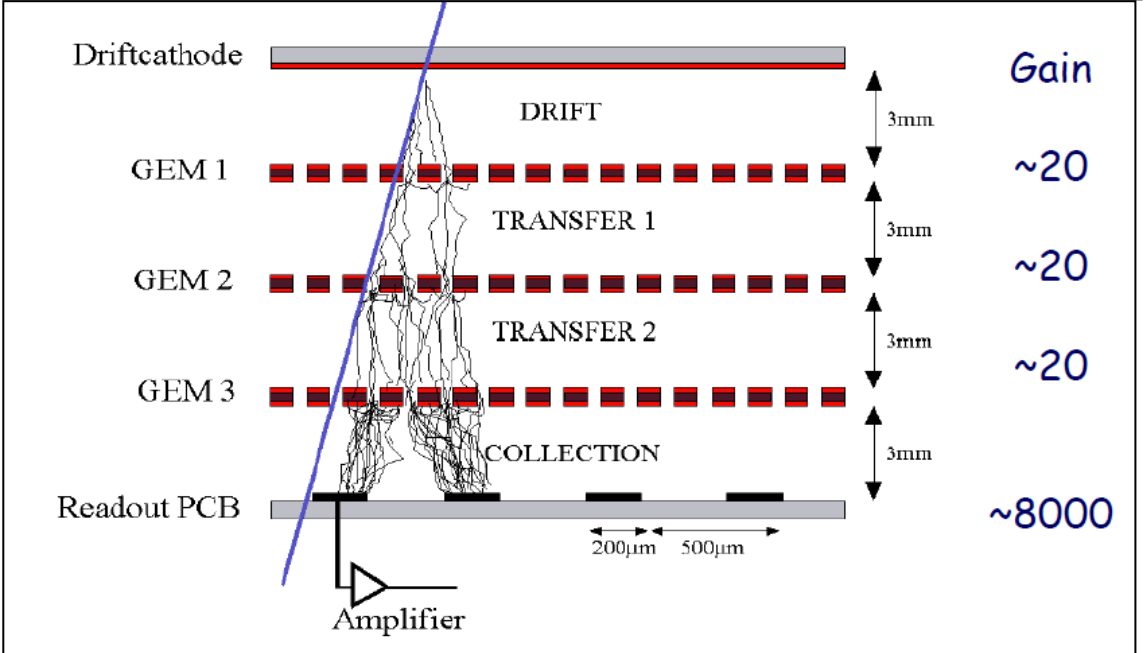
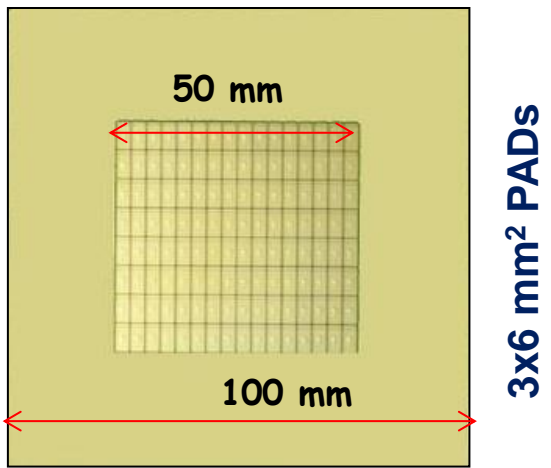
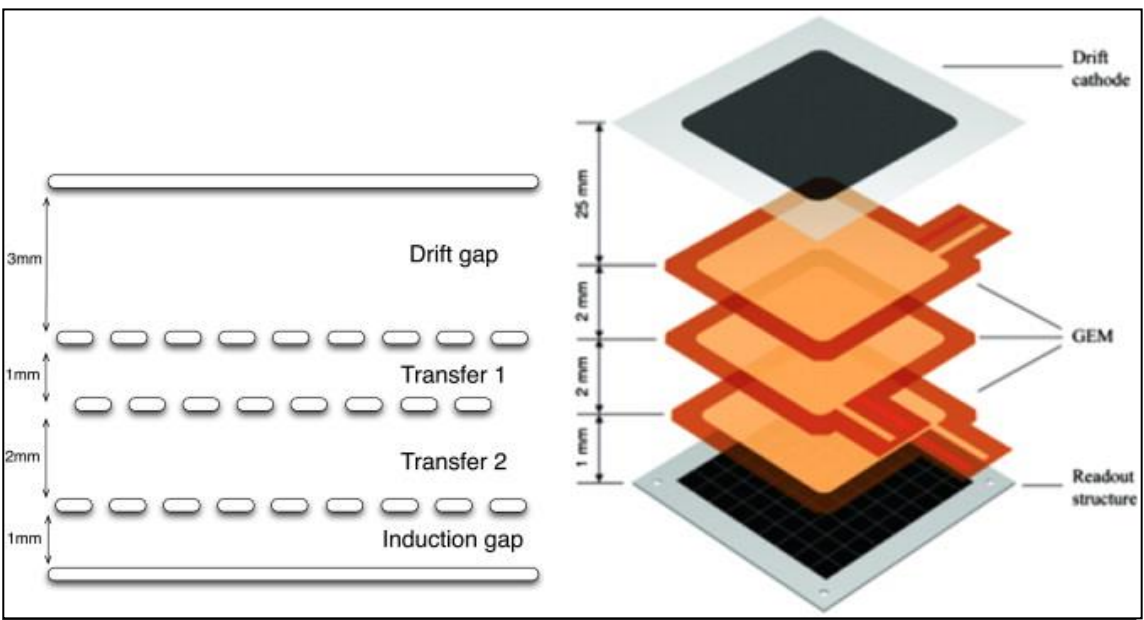
Gas Electron Multipliers (GEM)

Triple GEM configuration

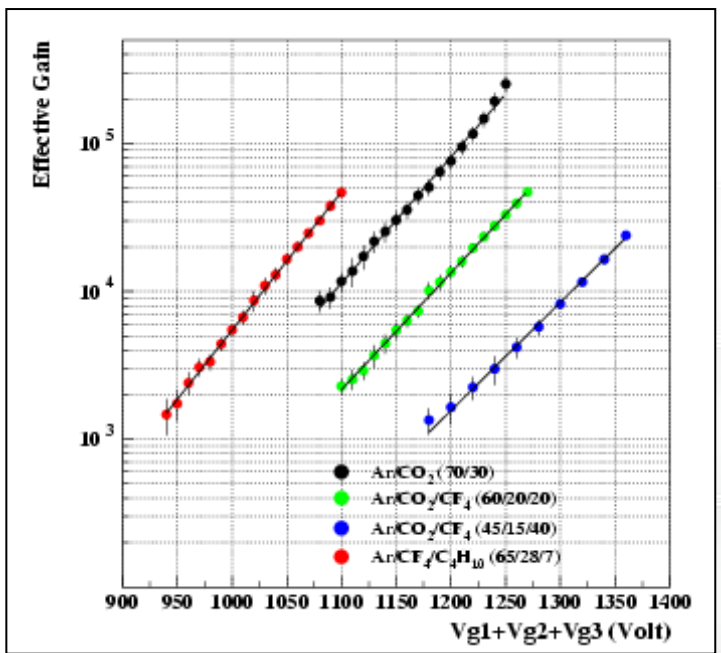


Layout of a typical Triple GEM detector constructed with standard 10 x 10 cm²

The anode has 128 pads. Each PAD can have a different geometry depending on detector applications.



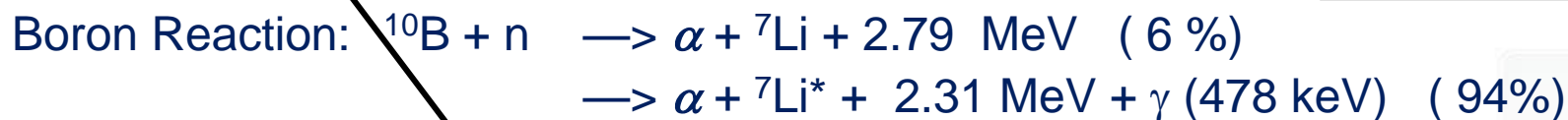
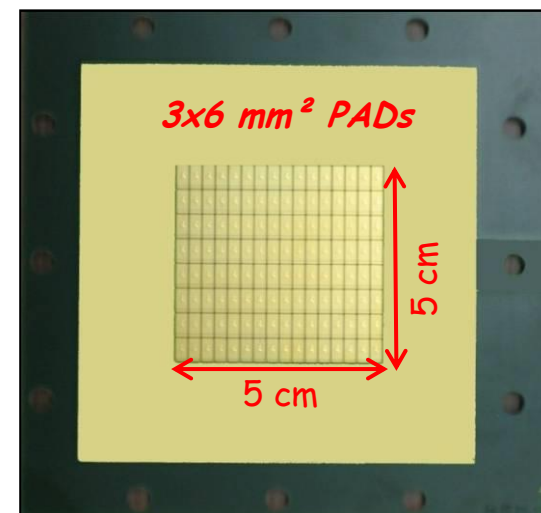
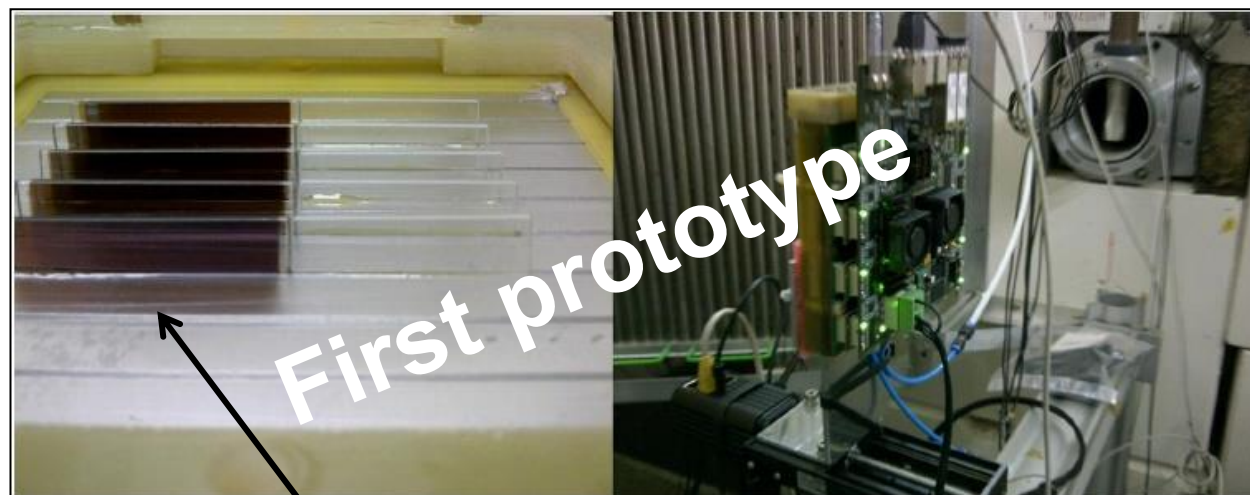
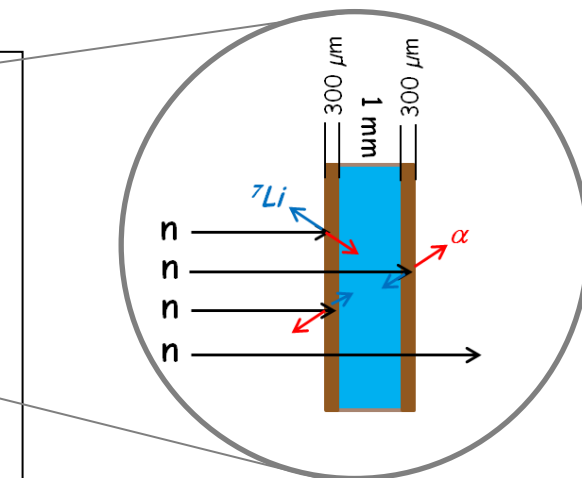
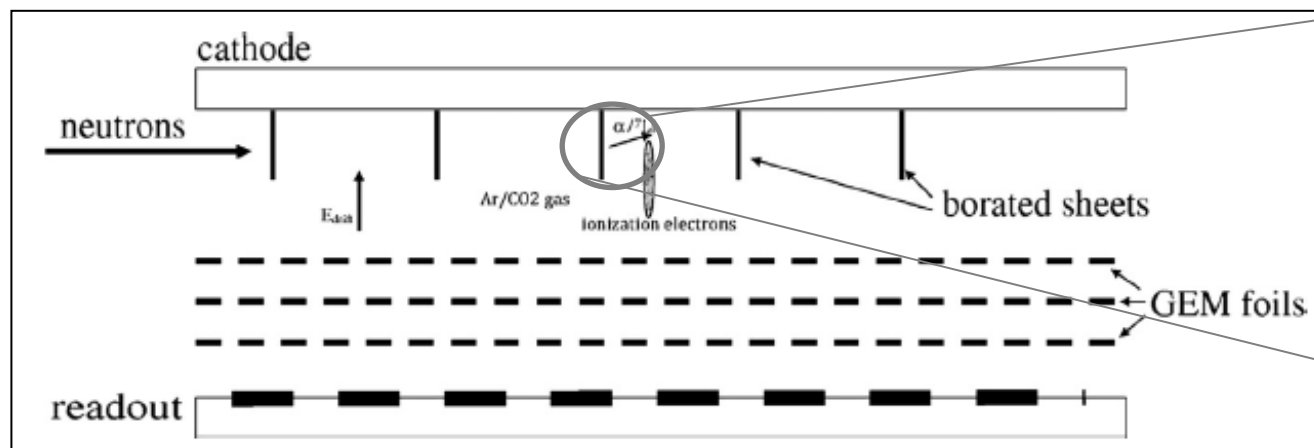
Gas Gain Curves



The sideon GEM (S-GEM) configuration for thermal neutrons



The idea was to insert a sequence of borated strips attached to the aluminum cathode. The drift region was extended and the detector was equipped with a side window.



Boron deposited by electron beam (thermal evaporation)

Tests @ TRIGA reactor (ENEA)



TRIGA Power: 1 MW (variable)

Beam line: radial channel

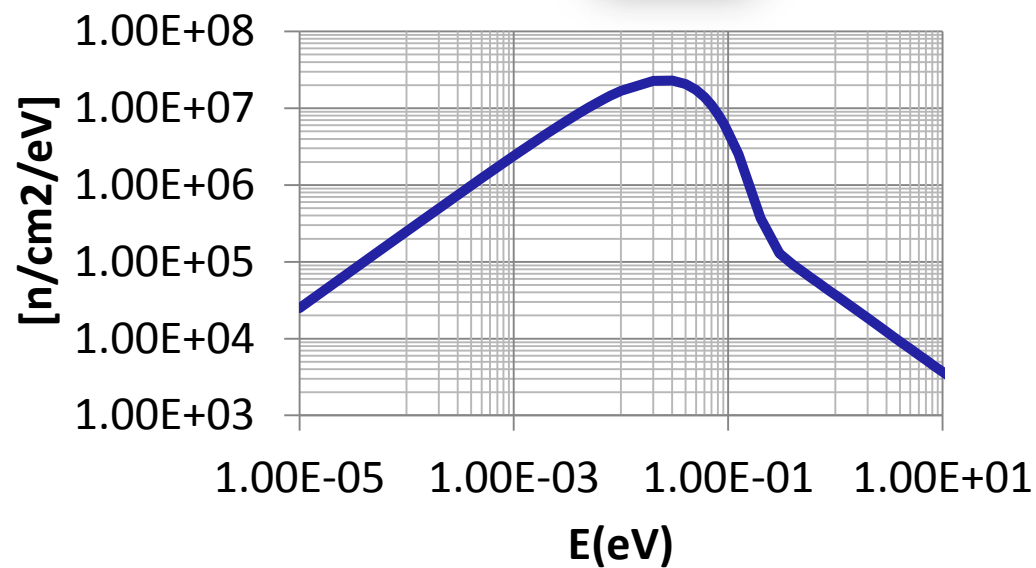
Flux @ 1 MW: $\phi = (2,3 \pm 0.2) \times 10^6 \text{ ncm}^{-2}\text{s}^{-1}$

Spectrum: Maxwell-Boltzmann at 25 meV

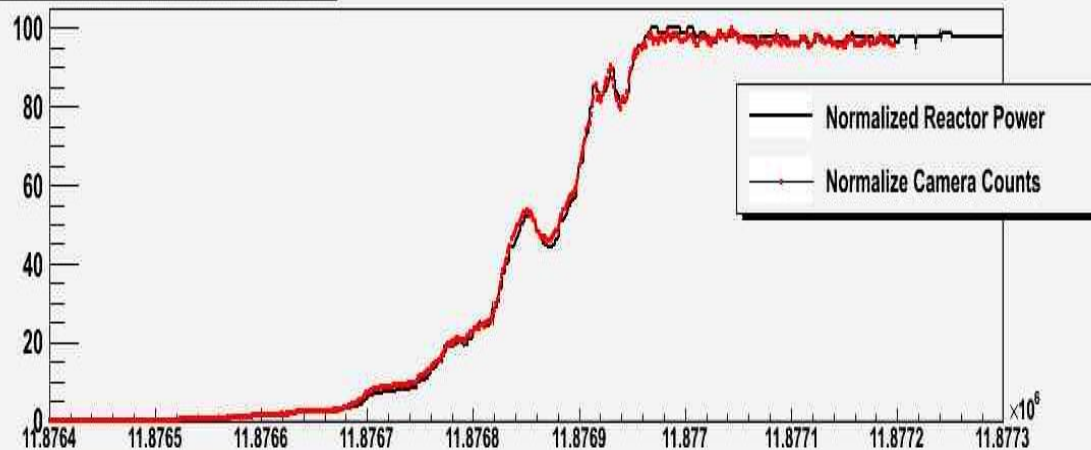
FWHM ~ 70 meV

The flux was changed varying the reactor power from 100 W to 1 MW.

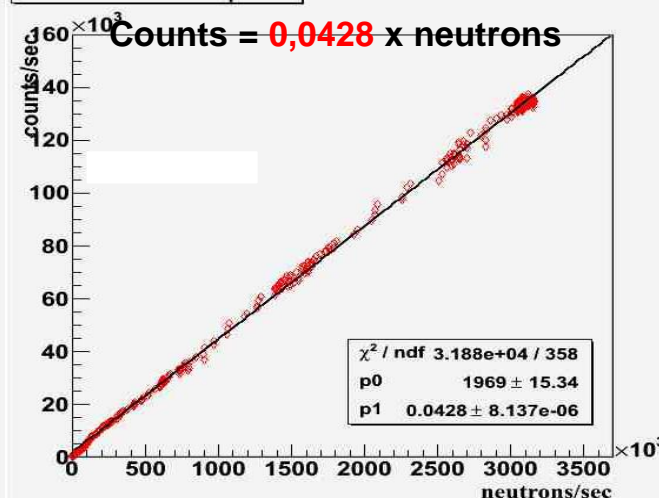
Side-on GEM detector was able to follow these variations.



Reactor Power & Detector Counts vs time



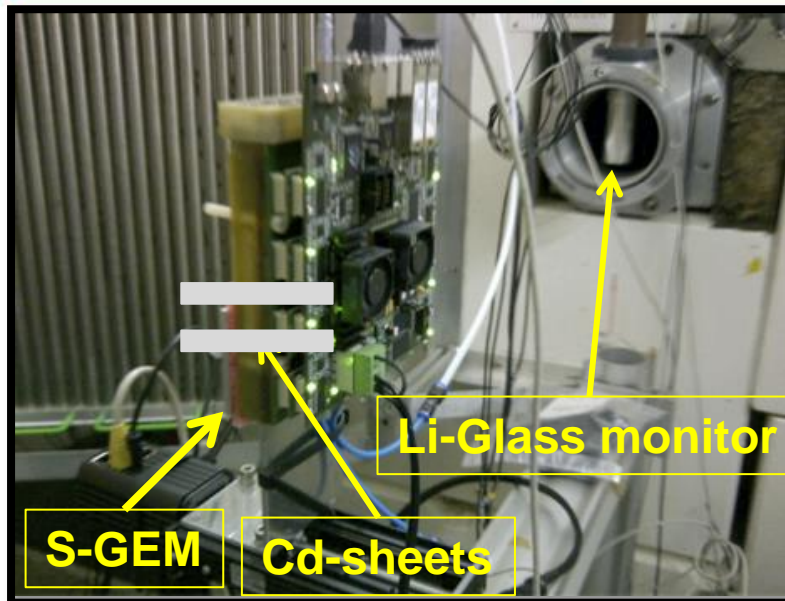
Detector Counts vs power



Knowing the incident flow and the detector active area of we estimated an **efficiency** of **$4.3 \pm 0,5\%$** , over the whole range of reactor thermal energies.

Test @ ISIS: ToF measurements

Beam line: ROTAX



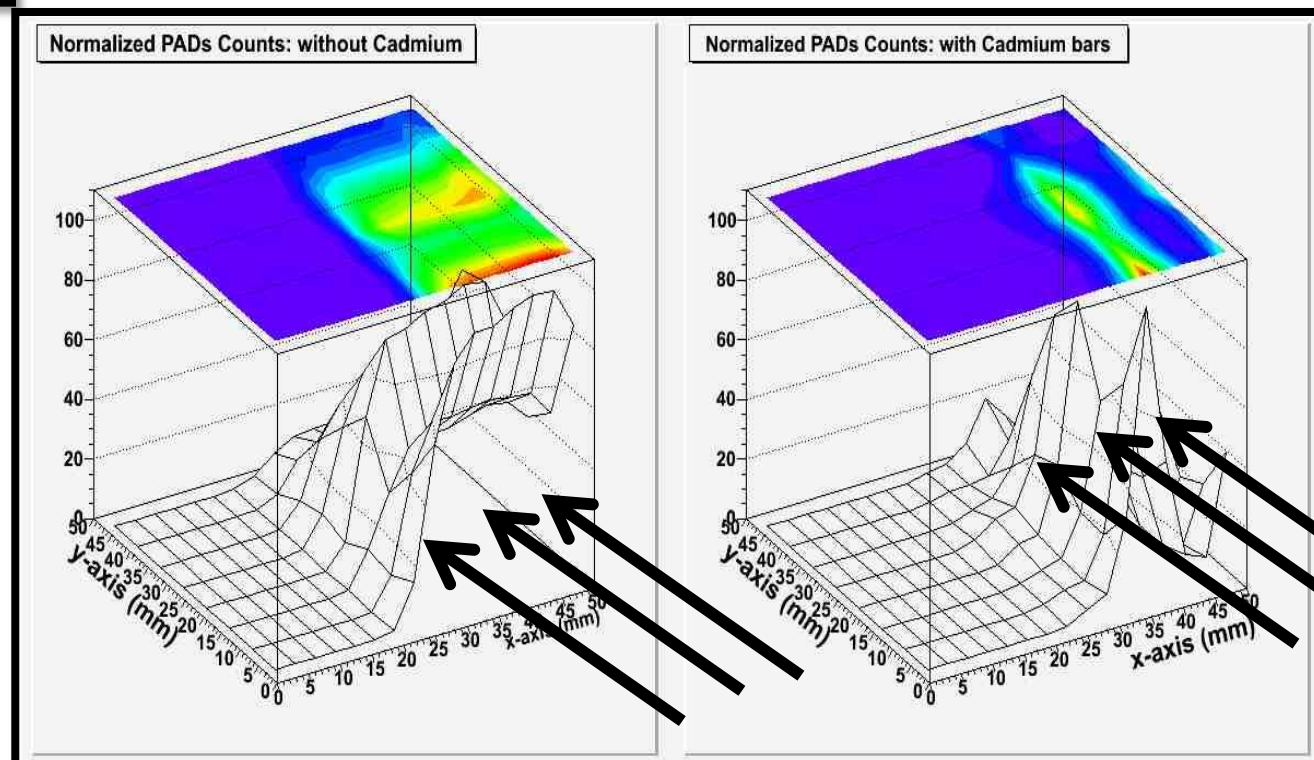
Stand alone detection system (not ISIS DAE)

An external trigger starts the detector acquisition of the detector which records data in a time window of 1 ms.

Reconstructed ToF spectrum from **S-GEM** measurement is in agreement with that obtained from the beam monitor of **ROTAX**.

2D intensity plots and the corresponding contour plots relative to the measurements with and without the cadmium sheets in front of the S-GEM. In the right panel, the counts are present in the region between the two absorbing Cd sheets.

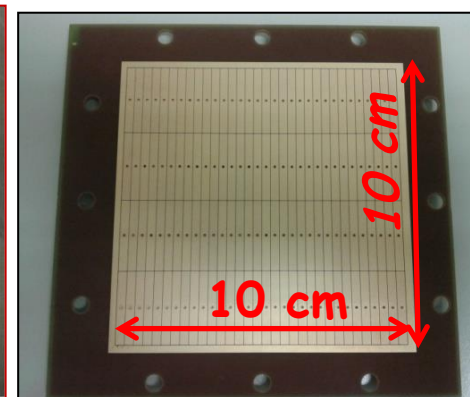
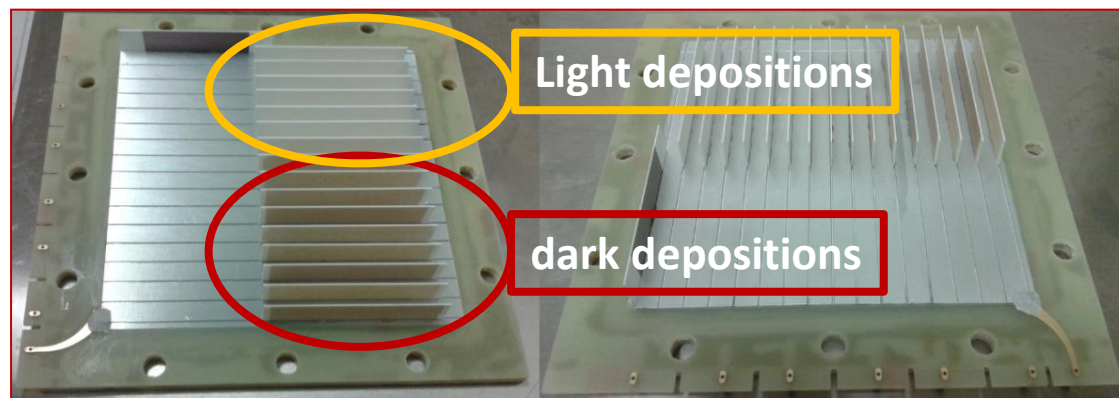
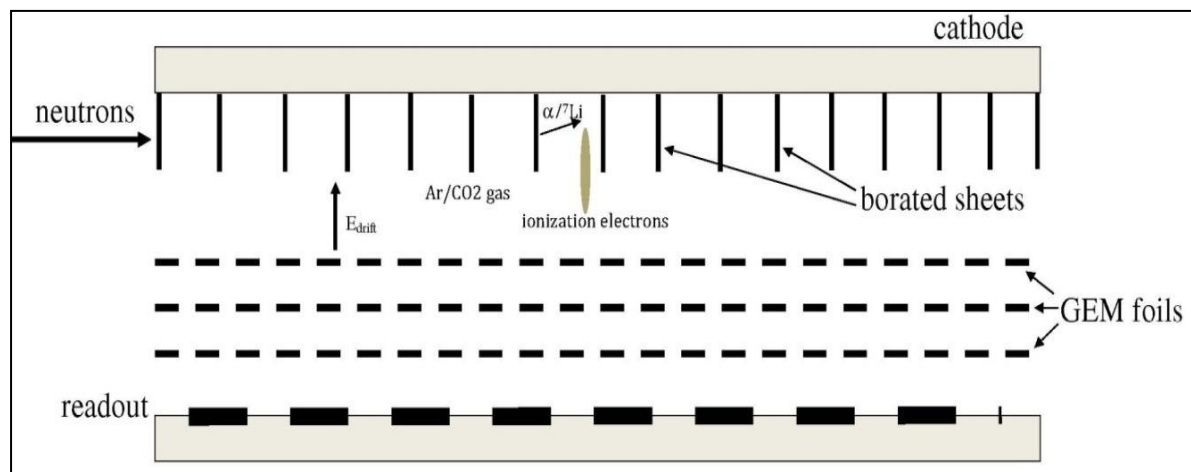
Signals from gamma-rays (10B/Cd and background) are effectively rejected at the chosen bias seen before.



The S-GEM second prototype



16 borated strips to obtain higher efficiency.

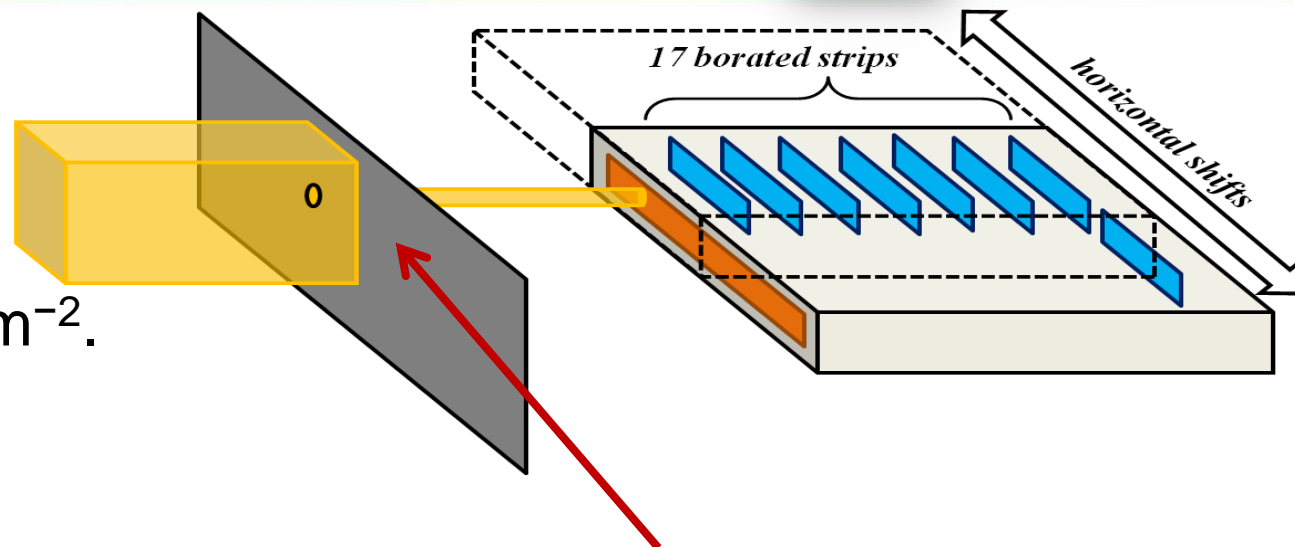


Anode with PADs having different geometry.
32x4 PADs each PAD is 3x24 mm².

ceramic strips (Al₂O₃) 400 μm thick.

Detector window is placed on the side of the anode with 32 PADs. In this way detector is able to measure also position of small spot beams impinging on the side-on window.

HFIR Power: 85MW
beam line: CG1A
 (detector test station)
estimated flux: $2 \times 10^6 \text{ n cm}^{-2}$.
 $\lambda_p \sim 4.23 \text{ \AA}$ ($E \sim 4.57 \text{ meV}$)
FWHM $\sim 0.11 \text{ \AA}$
irradiation area: $5 \times 5 \text{ cm}^2$
angular divergence: $< 1^\circ$



borated aluminum mask with a hole 2,5 mm in diameter

Comparison with ^3He gas tube at pressure

	S-GEM	^3He Tube
Overall mean counts [s^{-1}]	1863	6011
Background mean counts [s^{-1}]	21	1586
Signal/Background	87.7	2.8
Efficiency [%]	31	99

Deposition activity



From boron powder (enriched boron-10) solid targets for e-beam thin film deposition were produced at ENEA Frascati Research Centre.

Possible air contamination during targets sinterization.

Indeed darker depositions were obtained by using rough gross powder (prototype 1-glass sheets) targets rather than targets sinterized from fine powder.

We asked support to a private industry to produce sputtering targets in controlled environment and high-T and high-P to have less porous targets.



Columbus Superconductors SpA is a **world leader in cutting-edge magnesium diboride (MgB_2) technology** and the transformation of this superconducting material into long, versatile and **highly reliable superconducting wires**.



The company is vertically integrated, from R&D to applications and from production to sales.



Columbus is equipped with a comprehensive system for the processing of boron related powders and bulks



Initial boron pellet optimization was performed in air to find right parameters



Once optimized the pressing process, pellets were pressed in glove box and sintered in argon gas



Pellets are now realized and analyzed before shipment, both with natural boron as well as ^{10}B

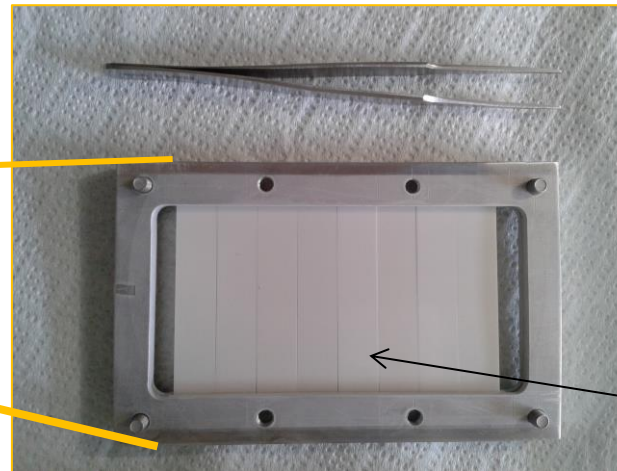


First boron targets will be shipped to INFN during this week

Deposition facilities (ENEA Frascati)



9 sheets can be simultaneously deposited on both sides



Alumina sheet
 $10 \times 50 \times 0.5$ mm

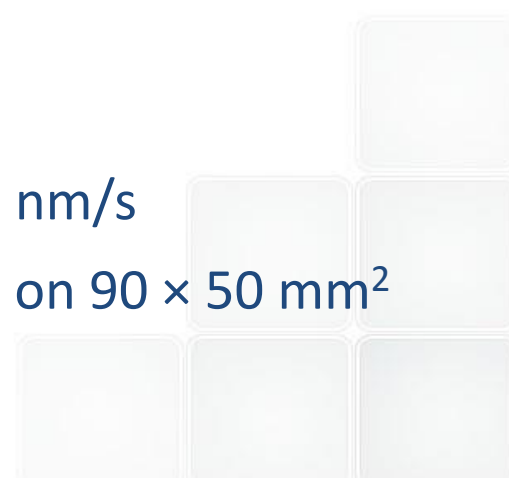
Evaporation system: Thermionics 10 kW (10 kV, 1 A), 4 crucibles (25 cc)

$d_{T-S} = 30$ cm

Maximum growth rate: 0.75 nm/s

Thickness uniformity: > 90% on 90×50 mm² area

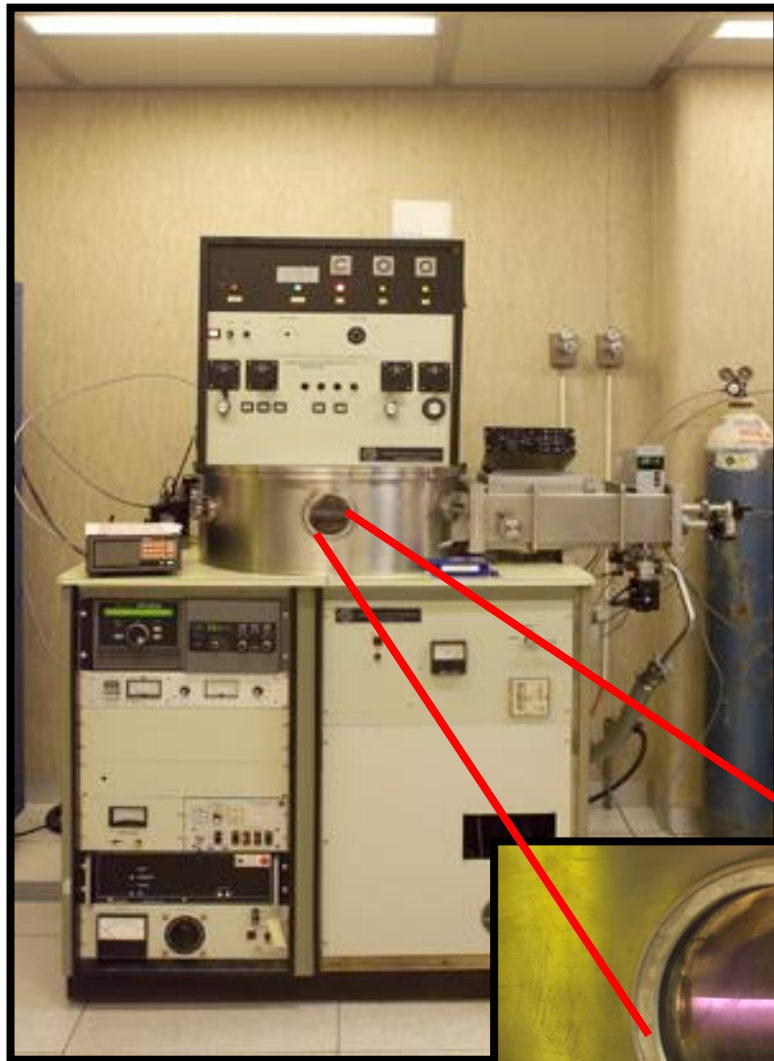
High Vacuum systems e-beam device for film depositions in the superconductivity Laboratory of the **Fusion Department** of the **ENEA** Frascati research Centre



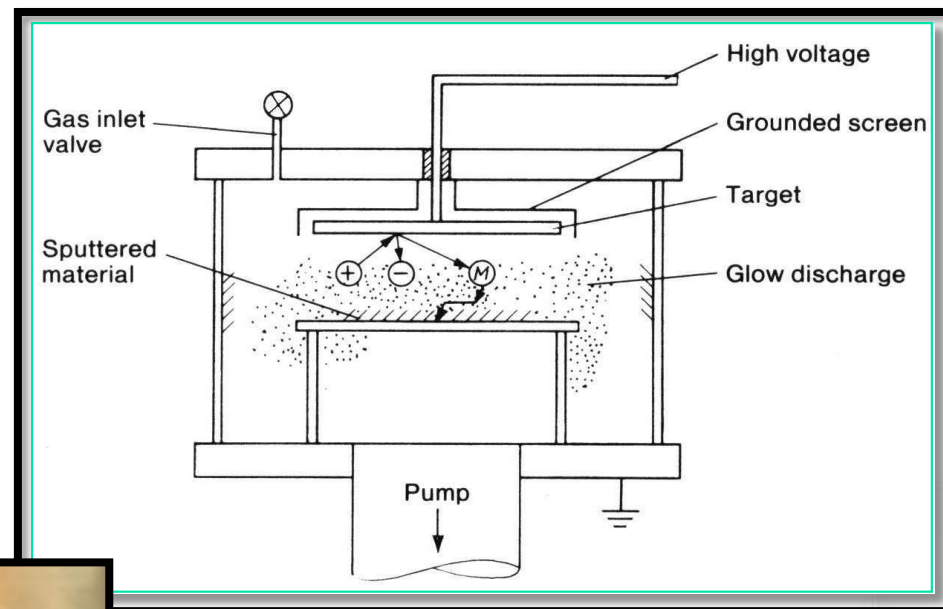
Deposition facilities (ENEA Casaccia)



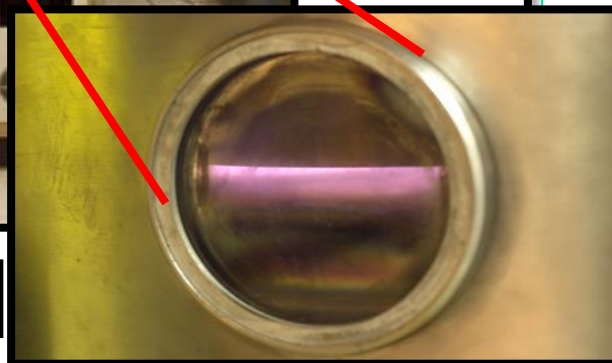
● Deposition systems: *radiofrequency sputtering*



- Radiofrequency sputtering system with 3 cathodes was used (target diameter 6.5 inches)
- Well suited for thin film deposition over 100 cm² surfaces



Glow discharge



Typical working
pressure $\sim 10^{-3}$ mbar

Deposition facilities (INFN-LNF)

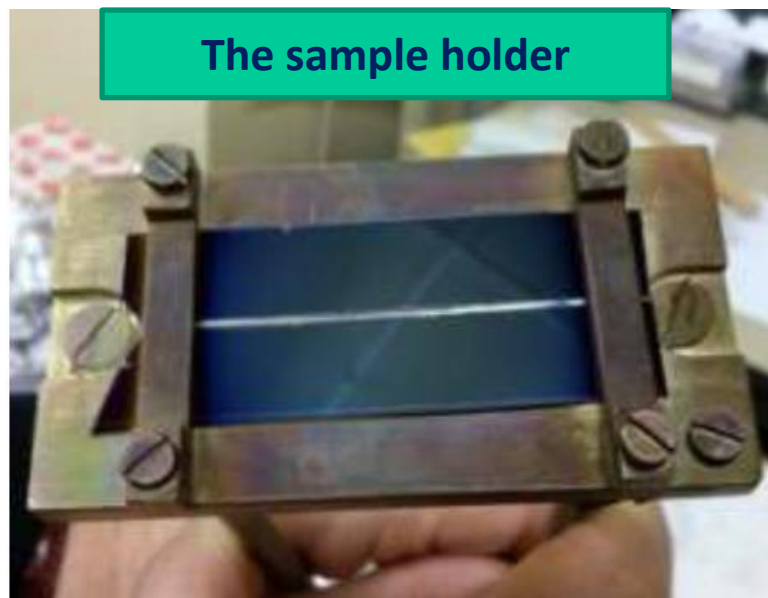
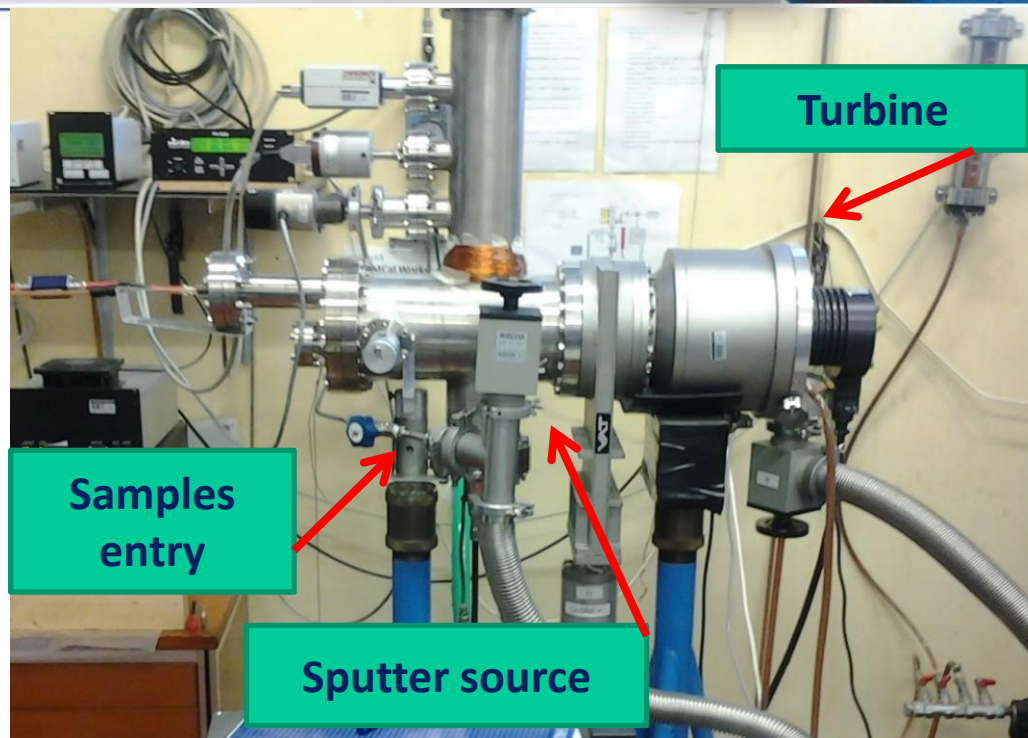


Sputtering deposition device

High Power Impulse Magnetron Sputtering (HPIMS) sputtering. The sputtering source is a MAK 2" (50,8 mm).

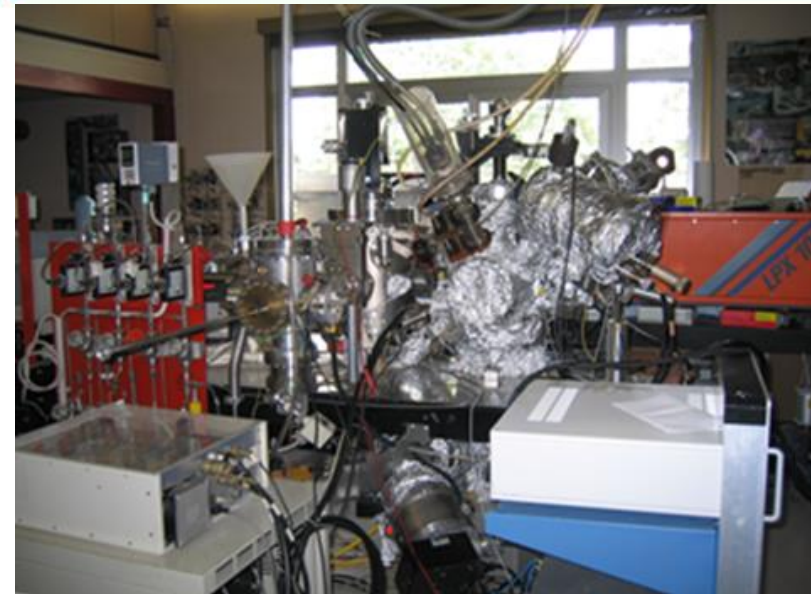
Since October 2014 we are performing depositions of boron on rectangular silicon sheets (50 mm x 10 mm).

A control unit attached measures the thickness of the deposition by the oscillation frequency of a crystal placed inside the chamber.



Features	Our settings
Power	100 W - RF
Distance target-substrate	50 mm to 120 mm
Thickness of the deposition	500 nm to 1200 nm
Deposition Rate	8 nm /min
Vacuum	10E-6 mbar
Pressure Argon	10E-3 mbar

Characterization tools (ENEA Frascati)



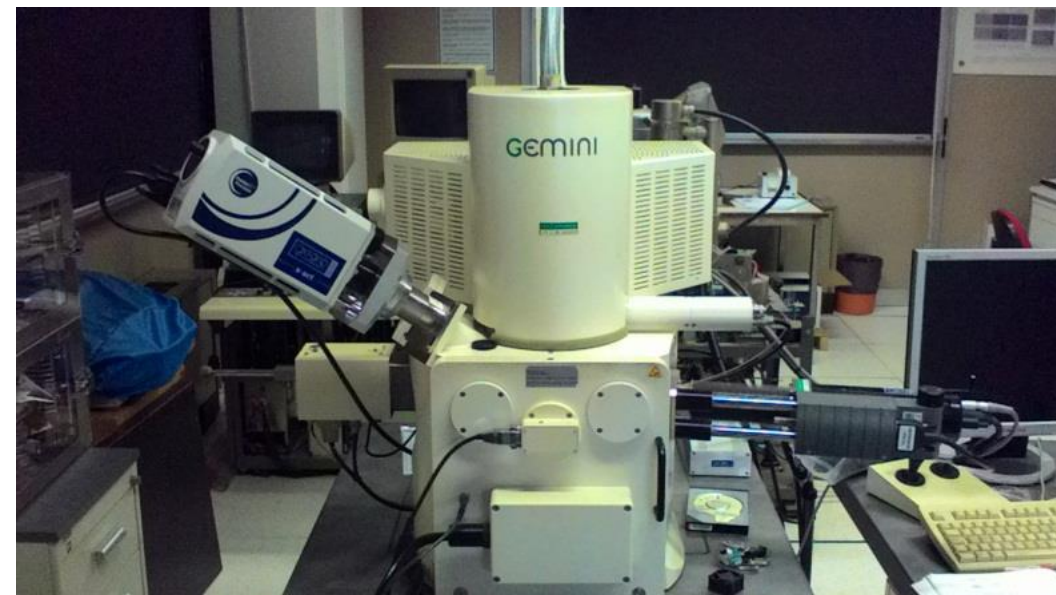
The XPS acquisition system operates in an ultra-high vacuum system with 4×10^{-8} Pa base pressure.

It is equipped with a VG Al $K\alpha$ monochromatized x-ray source and a CLAM2 hemispherical analyser.

Morphological characterization was performed with a Leo 1525 field emission scanning electron microscope (SEM) equipped with in-lens annular detector



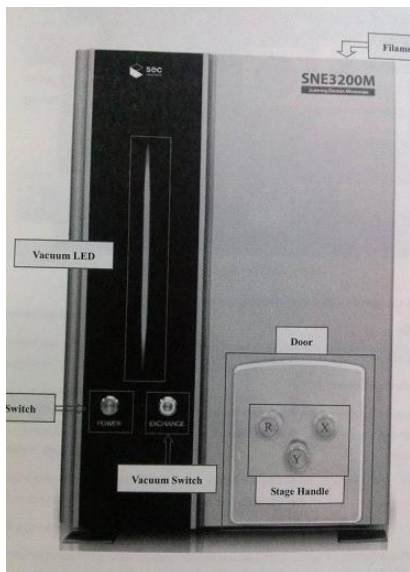
Atomic Force
Microscope



Characterization tools (INFN-LNF)

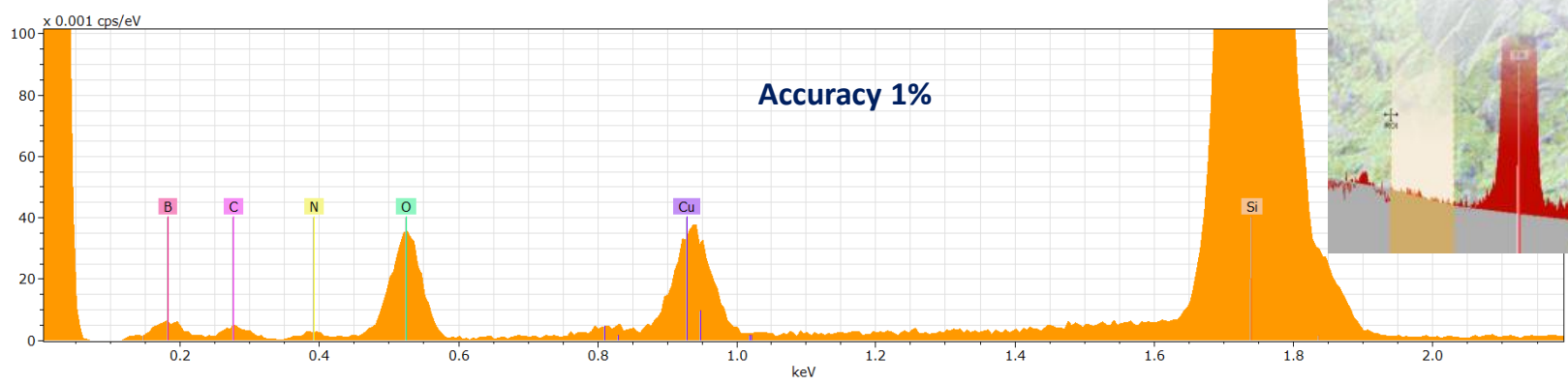
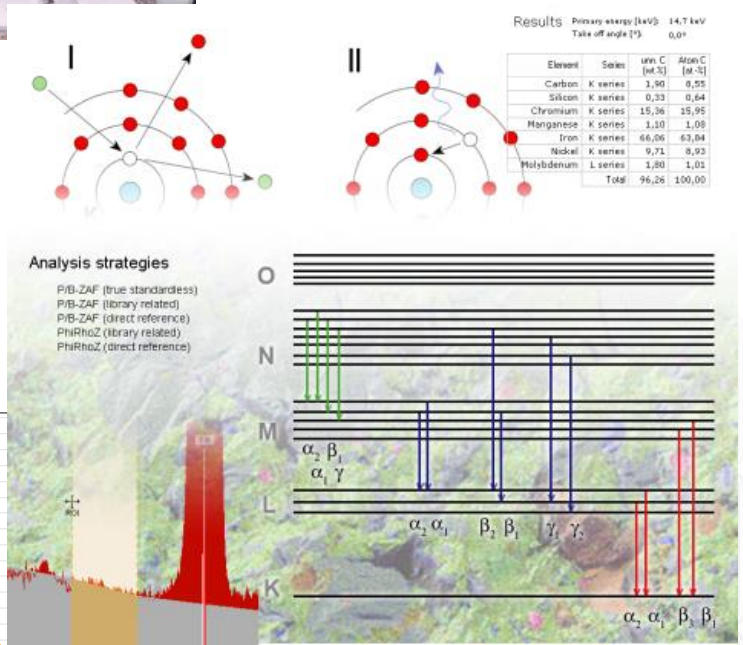


Scanning Electron Microscope equipped with a X-flash detector



SE and BSE provide images of the specimen, revealing surface structure and topology. The X-ray spectrometer provides detailed information about chemical composition.

The energy of the characteristic X-rays is nearly independent of the chemical bonding state of the affected atoms; the electron probe microanalysis (EPMA) is element sensitive. In the resulting energy dispersive spectrum X-rays correspond to visible peak to identify.



Leica DCM-3D non contact profilometer

confocal and interferometric profilometry

The very low depth of field intrinsic of confocal microscopy is used to make z-scan maps of a sample;

2 nm z resolution at 150x magnification, 0,95 NA;

Use of a Mirau interferometer to measure even steps as small as 0,1 nm;

Lateral resolution diffraction limited, same as a conventional blue light microscope.



Keysight G200 Nanoindenter

Indenter using a three-sided diamond tip to obtain depth profiled elastic modulus and hardness plots;

2 measuring heads, a high displacement resolution (10 pm) and an ultrahigh resolution one (0,2 pm);

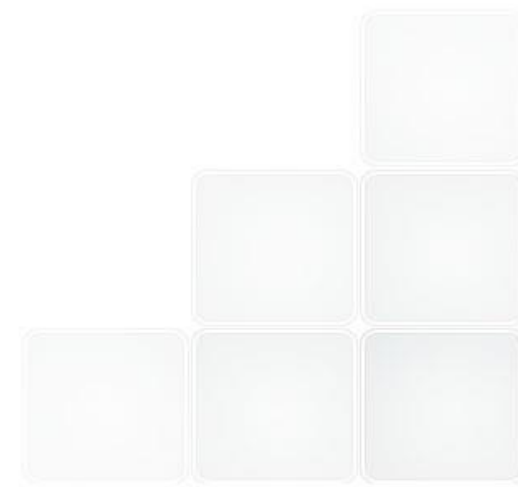
High speed mode capable of one indentation/sec;

High resolution head capable of scratch testing, lateral force resolution 2 μN , normal force resolution 0,05 μN .



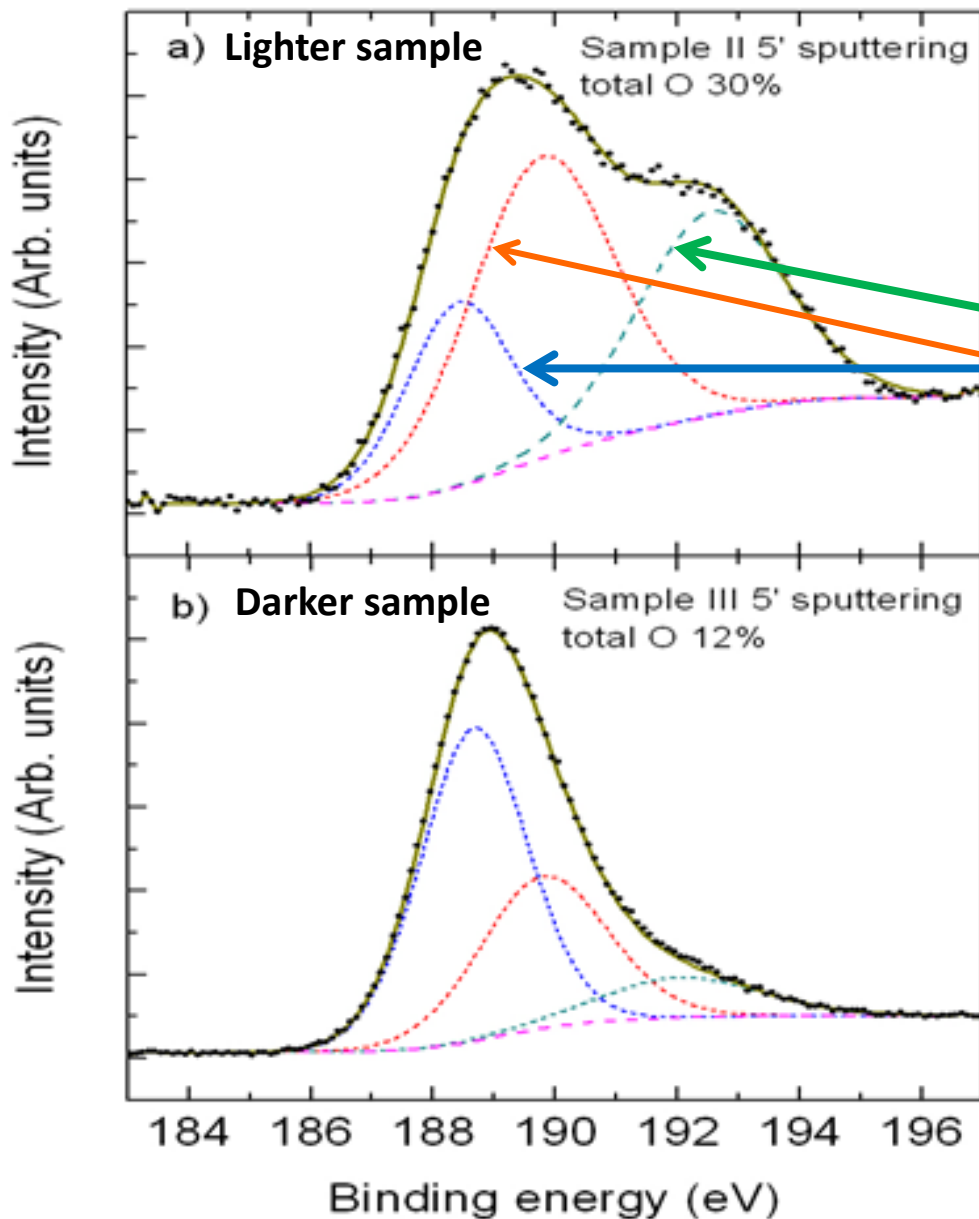


A brief overview on preliminary results



X-Ray Photoelectron Spectroscopy-XPS

surface chemico-physical analysis



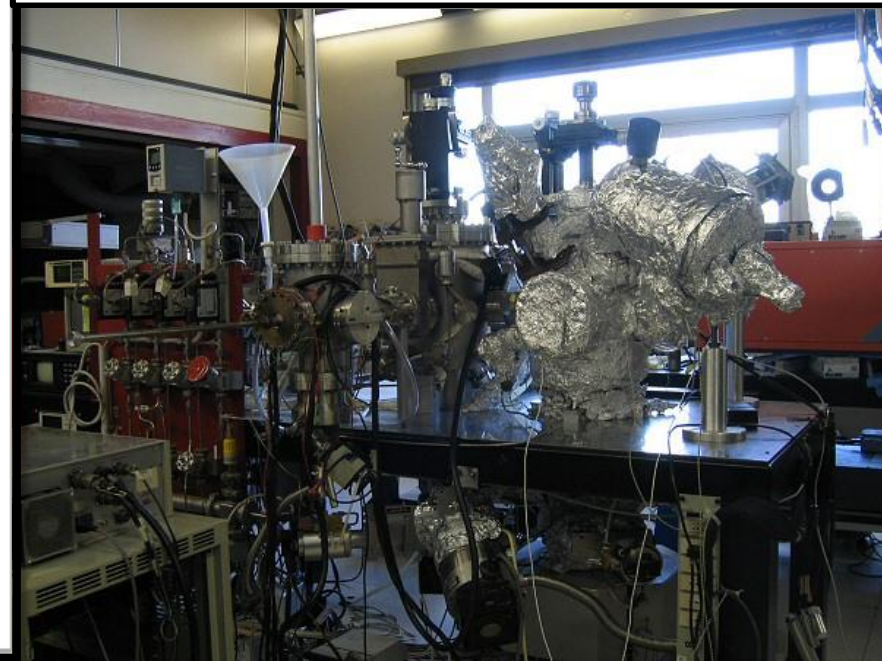
XPS spectra of depositions

E_B scan around the boron peak (tables)
3-components fit indicate chemical composition made of:

metallic Boron



A pure element would appear as a Gaussian distribution

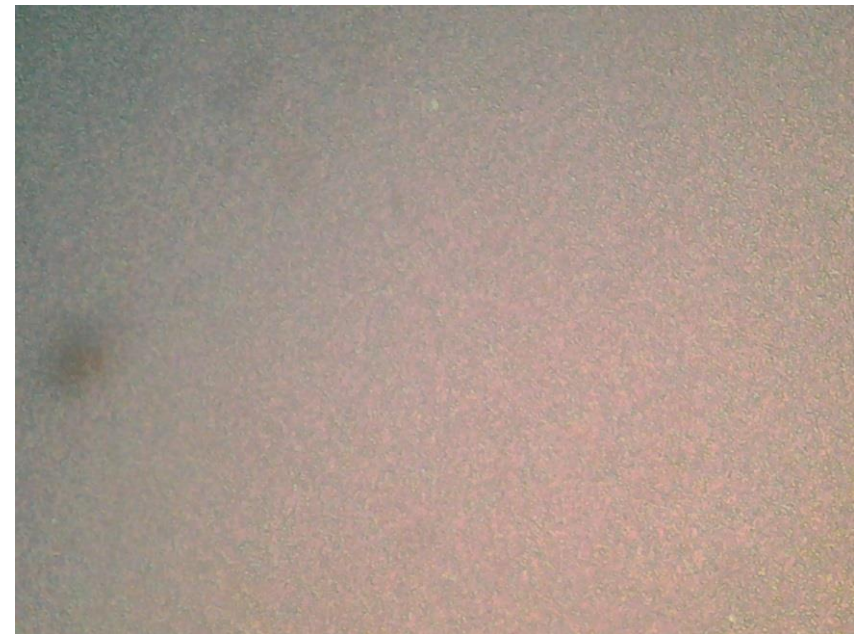
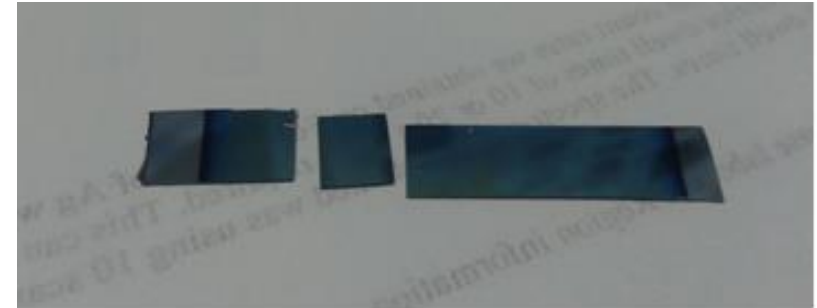


A new set of depositions

INFN sputtering system

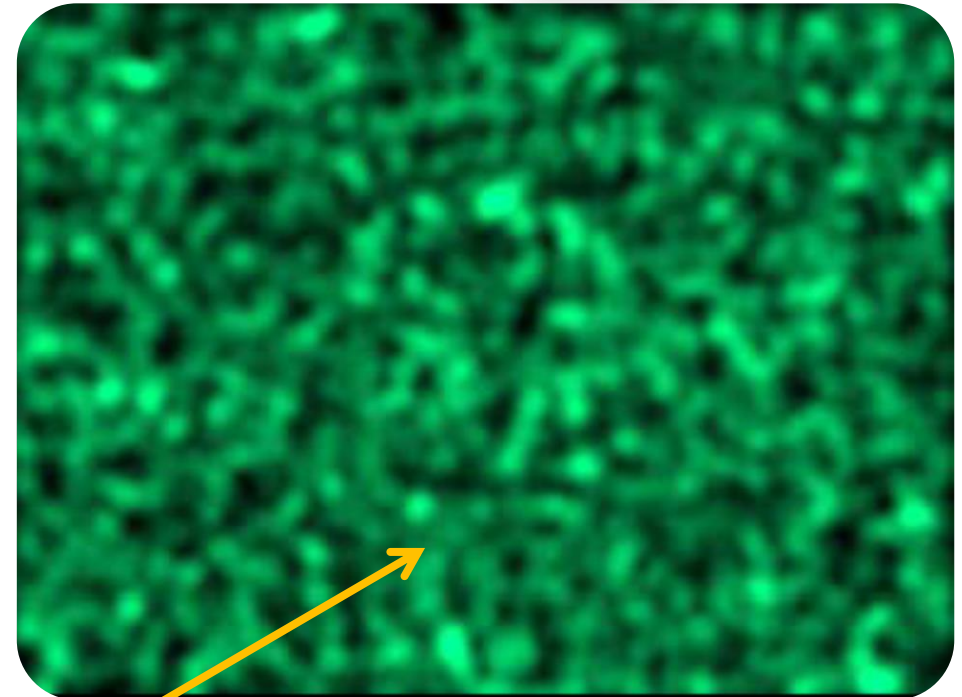
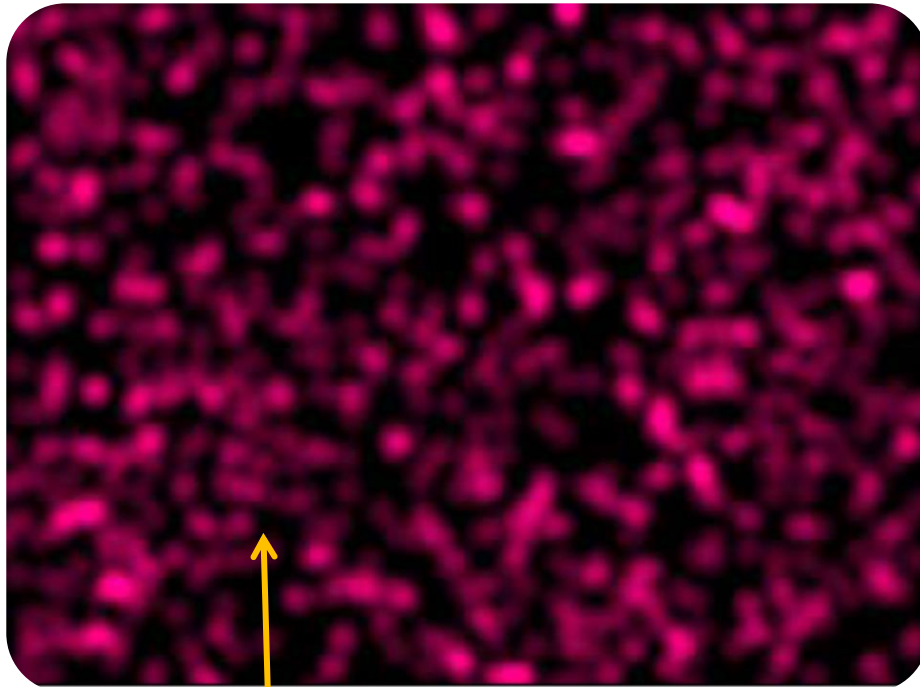


- We have been completed over 40 depositions on silicon by changing:
 - Type of silicon used,
 - Target-sample distance
 - Sample pre-treatment (etching, heating...)
 - B film thickness.
- Analyses were conducted using profilometry, SEM, optical microscope (500 x) and tape test to evaluate the adhesion “on the fly”
- The figure on the right shows a particularly homogeneous coating (500X) of a deposition from 1 μm
- The profilometer confirms the presence of a coating of 600 nm of boron
- Further research will be carried out to stabilize the oxidation reactions of boron. Oxidation leads to a strong degradation of the deposition.

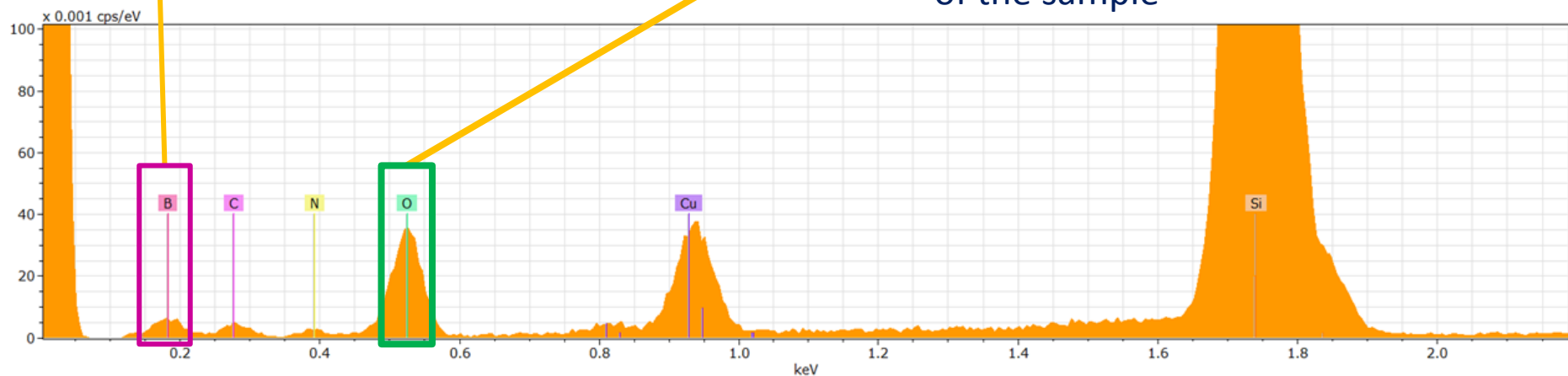


SEM + X-flash detector

Microanalysis tool



Fixing x-ray energy one obtains an intensit 2D map scanning a given area of the sample



Conclusions



- ✓ We developed a side-on GEM-based thermal neutron detectors to reach high efficiency (50%) @ 25 meV neutron energy.
- ✓ The main activity to reach the goal is the deposition of **pure ^{10}B** films (not an easy task) rather than B_4C onto proper substrates (glass as a first attempt, alumina, aluminum and silicon).
- ✓ We started with e-beam but we are using/will use sputtering and Pulsed Laser Deposition
- ✓ We are using targets sinterized in a controlled environment and due (P,T) conditions to provide not porous target reducing internal oxidation.
- ✓ We are supported after deposition by several and complementary tools for mechanical and chemico-physical analysis of the deposited films

Side-On GEM Collaboration network (deposition and on beam testing)

GEM SIDEON IS BEING DEVELOPED WITHIN
A COLLABORATION OF PEOPLE COMING
FROM DIFFERENT INSTITUTIONS AND
WITH DIFFERENCE COMPETENCES



E. Aza (CERN)
E. Bemporad (Roma Tre)
S. Cappello (INFN-LNF)
G. Celentano (ENEA)
G. Claps (ENEA)
G. Croci (CNR)
A. Grilli (INFN-LNF)
S. Loreti (ENEA)
R. Moscatelli (Roma Tre)
F. Murtas (INFN-LNF)
A. Pietropaolo (ENEA)
L. Quintieri (ENEA)
D. Raspino (ISIS)
R. A. Riedle (Oak Ridge)
M. Renzelli (Roma Tre)
A. Rufoloni (ENEA)
A. Santoni (ENEA)

E. Soldani (INFN-LNF)
A. Sytchkova (ENEA)
A. Vannozzi (ENEA)
A. Viticchiè (INFN)

Ongoing activity involves:

- **Italian Institute of Technology**
- **Columbus**

Some results already published

S-GEM tests:

- NIMA A **729** (2013) 117–126
- EPL, **105** (2014) 22002

Deposition analysis

- Surf. Coat. Tech. in press (march 2015)

Color legend

Black:	test on beam
Red:	mechanical characterization
Yellow:	Chemico-physical analysis
Green:	MC simulation
Violet:	deposition